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Stocking Distributor

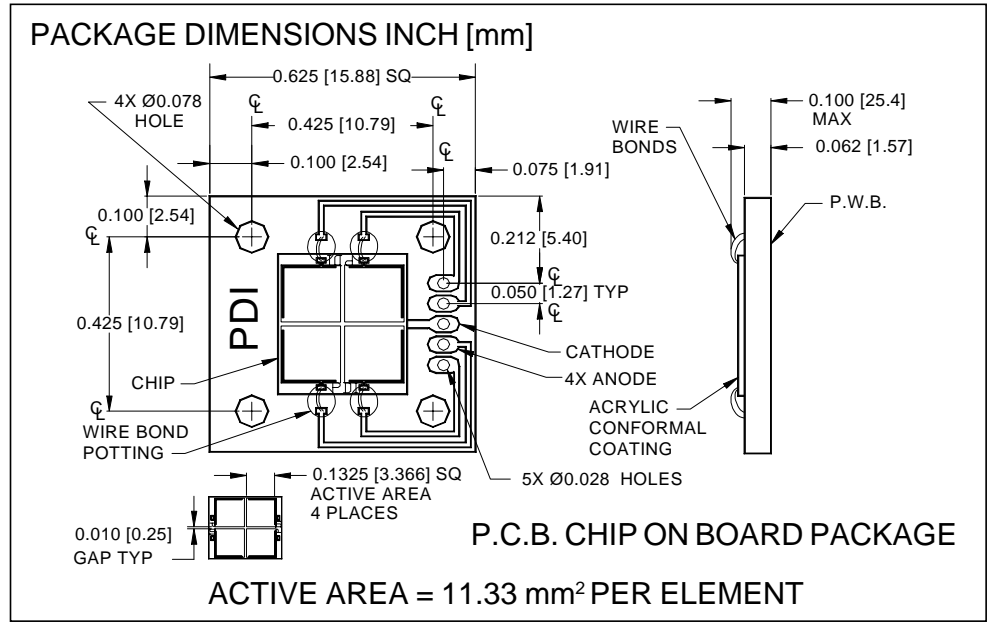
Click to view price, real time Inventory, Delivery & Lifecycle Information:

[Advanced Photonix, Inc.](#)
[PDB-C206](#)

For any questions, you can email us directly:

sales@integrated-circuit.com

**Silicon Photodiode, Blue Enhanced Photoconductive
Quadrant Type PDB-C206**



FEATURES

- Narrow gap
- P.C.B. mount
- Blue enhanced
- Large active area

DESCRIPTION

The **PDB-C206** is a silicon, pin planar diffused, blue enhanced large area quadrant photodiode. Each element is 11.33 mm² with a .010 inch (0.25 mm) gap. Packaged on a .062 inch thick P.C.B. chip on board.

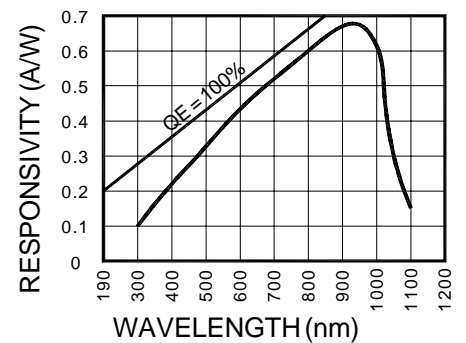
APPLICATIONS

- Optical alignment
- Position sensing
- Edge sensing
- Instrumentation

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS
V _{BR}	Reverse Voltage		100	V
T _{STG}	Storage Temperature	-50	+125	°C
T _O	Operating Temperature Range	-40	+100	°C
T _S	Soldering Temperature*		+240	°C
I _L	Light Current		0.5	mA

SPECTRAL RESPONSE



ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _{SC}	Short Circuit Current	H = 100 fc, 2850 K	100	185		μA
I _D	Dark Current	H = 0, V _R = 10 V		10	50	nA
R _{SH}	Shunt Resistance	H = 0, V _R = 10 mV	50	100		MΩ
TC _{RSH}	R _{SH} Temp. Coefficient	H = 0, V _R = 10 mV		-8		% / °C
C _J	Junction Capacitance	H = 0, V _R = 10 V		50		pF
λ _{range}	Spectral Application Range	Spot Scan	350		1100	nm
λ _p	Spectral Response - Peak	Spot Scan		950		nm
V _{BR}	Breakdown Voltage	I = 10 μA	50	75		V
NEP	Noise Equivalent Power	V _R = 10 V @ Peak		1.0x10 ⁻¹⁴		W/√Hz
tr	Response Time	R _L = 1 KΩ V _R = 10 V		25		nS